

Features

- Small (10.4 x 6.0 x 2.2mm)
- Excellent bias repeatability over temperature
- Dual-axis MEMS accelerometer in a hermetically sealed ceramic LCC surface mount package for temperature and humidity resistance
- Five dynamic range options; ±0.85g, ±2.5g, ±10g, ±30g ±96g
- Analogue and digital (SPI®) outputs for linear acceleration and temperature
- Wide bandwidth (typically 170Hz digital, 250Hz analogue)
- Temperature range -40 to +125ºC
- Low power consumption (3mA Typ) from a 3.3V supply
- Integral temperature sensor
- RoHS compliant

Applications

- Aerospace and industrial
- Aircraft AHRS and controls
- Platform stabilisation
- Drilling guidance
- Surveying and mapping
- Land and marine navigation
- Transportation
- Inertial measurement units
- Levelling and tilt sensing

1 General Description

Gemini™ is a new family of integrated MEMS accelerometers from Silicon Sensing, providing high performance dual-axis linear acceleration measurement in a small surface mounted package. It comprises a dual-axis MEMS sensing device with a dedicated control ASIC in a single ceramic LCC package. Sensor data is output via analogue and digital (SPI®) interfaces.

The CAS200 series of parts provides two in-plane axes of linear acceleration sensing and is available in five different dynamic ranges:

- ±0.85g CAS211
- ±2.5g CAS212
- $±10g CAS213$
- ±30g CAS214
- ±96g CAS215

CAS200 is supplied as a PCBA surface mountable standard LCC ceramic packaged device, which is hermetically sealed providing full environmental protection.

Precise linear acceleration sensing is achieved by a Silicon MEMS detector forming an orthogonal pair of sprung masses. Each mass provides the moving plate of a variable capacitance formed by an array of interlaced 'fingers'. This structure also provides critical damping to prevent resonant gain. Linear acceleration results in a change of capacitance which is measured by demodulation of the square wave excitation.

Figure 1.1 CAS200 Functional Block Diagram

2 Ordering Information

3 Specifi cation

Unless otherwise specified the following specification values assume Vdd = 3.15 to 3.45V over the temperature range -40 to +125°C.

3.1 Digital Output Specifi cation

Note 1:

The bias setting error is a fixed offset, set with 3.3V applied to the device. This bias may change for other applied voltages and can be removed by external compensation.

3.2 Analogue Output Specifi cation

Note 2:

The acceleration outputs are at a nominal Vdd/2 voltage. Typical variation from device to device is ±10.0mV, and may change with variation in power supply voltage. The fixed offset can be removed by external compensation.

Specification Continued

4 Absolute Minimum/Maximum Ratings

Notes:

Exposure to the Absolute Maximum Ratings for extended periods may affect performance and reliability.

5 Typical Performance Characteristics

Graphs showing typical performance characteristics for Gemini™ are shown below: **Note:** Typical data is with the device powered from a 3.3V supply.

Typical Performance Characteristics Continued

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Typical Performance Characteristics Continued

Typical Performance Characteristics Continued 1.50 1.50 1.00 1.00 Normalised SF Error (%) **Normalised SF Error (%)** Normalised SF Error (%) **Normalised SF Error (%)**0.50 0.50 0.00 0.00 -60 -40 -20 0 20 40 60 80 100 120 140 -60 -40 -20 0 20 40 60 80 100 120 140 -0.50 -0.50 -1.00 -1.00 -1.50 -1.50 **Temperature (°C) Temperature (°C) Figure 5.21 CAS211 (0.85g) Accelerometer X Figure 5.22 CAS212 (2.5g) Accelerometer X SF Error with Temperature SF Error with Temperature** 1.50 1.56 1.00 1.00 **Normalised SF Error (%)** Normalised SF Error (%) **Normalised SF Error (%)** Normalised SF Error (%) 0.50 0.50 0.00 0.00 -60 -40 -20 0 20 40 60 80 100 120 140 -60 -40 -20 0 20 40 60 80 100 120 140 -0.50 0.50 -1.00 -0.0 -1.50 1.50 **Temperature (°C) Temperature (°C) Figure 5.23 CAS213 (10g) Accelerometer X Figure 5.24 CAS214 (30g) Accelerometer X SF Error with Temperature SF Error with Temperature**

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Typical Performance Characteristics Continued

Temperature (°C)

Figure 5.25 CAS215 (96g) Accelerometer X SF Error with Temperature

6 Glossary of Terms

7 Interface

Physical and electrical inter-connect information.

7.1 Physical and Electrical Interface, Pad Layout and Pinouts

All dimensions in millimetres.

Figure 7.2 Recommended Pad Layout

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Figure 7.3 Analogue Output Setup

Figure 7.4 Digital Output Setup

Note: The Gemini accelerometers are capacitive sensors. The routing of signal tracks beneath the package (including power supply signals connecting to starpoints) can cause an offset in accelerometer bias. If such routing is unavoidable, the resulting offset can be removed by compensation at the higher system level.

Table 7.1 Input/Output Pin Definitions

Table 7.2 Electrical Characteristics

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7.2 Digital Interface

This section defines the SPI® interface timing and the message types and formats to and from the Gemini[™] CAS200 sensor.

The SPI® interface, when selected, will be a 4-wire interface with the following signals:

Signal electrical characteristics are defined in Table 7.3.

Table 7.3 SPI® Electrical Characteristics

SPI_SELECT, SPI_CLK and SPI_MOSI all have internal pull-up resistors in the sensor ASIC.

SPI_MISO is held in tri_state if SPI_SELECT is High and is driven if SPI_SELECT is Low.

7.3 Signal Timing

The interface will transfer 6 bytes (48 bits) in each message. The message rate will be 1kHz (recommended), (1Hz-min, 10kHz-max) with a SPI® clock frequency of 1MHz (nom), (100kHz-min 8MHz-max). A sampling rate greater than 500Hz is recommended to reduce the effects of aliasing.

The sensor will be a slave on the interface. All accesses shall use SPI® Mode 0.

Figure 7.5 specifies the interface timing for correct operation.

Figure 7.5 SPI® Timing Diagram

7.4 SPI® Message Format

This section defines the types and formats of the messages to the GeminiTM sensor.

7.4.1 Messages to ASIC (MOSI)

The messages to the sensor shall be sent in the following order:

- Byte 1 Command Byte (transmitted first, MSB first)
- Byte 2 Data 1
- Byte 3 Data 2
- Byte 4 Data 3
- Byte 5 Data 4
- Byte 6 Checksum (see note 3)

Data Format:

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Message Data:

The following table defines the content of each byte of the input message.

Table 7.4 Message Content to GeminiTM

Example message data:

1. To request Acc Y and Acc X data only.

2. To request Status and Temperature.

3. To request CBIT and Acc Y and Acc X data.

4. To request CBIT and Status and Temperature.

7.4.2 Message from GeminiTM (MISO)

The messages from the sensor shall be sent in the following order.

- Byte 3: Data 2
- Byte 4: Data 3 Byte 5: Data 4
- Byte 6: Checksum (see notes 3 and 4)

The data is output in 2's complement format, most significant byte first.

Data Format:

The Status Byte content depends on the message requested.

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Message Data Content:

The output message data content will depend on the command byte from the previous input message. The content is indicated by bits (2:0) of the Status byte.

Table 7.5 Message Content from ASIC

Notes:

3. The checksum is the LS byte of the 1's complement of the first 5 bytes of message. If the checksum is incorrect the input message will be ignored and the checksum error flagged in the status byte of the next SPI® message. The content of the message following a bad checksum message shall be the message type selected in the last 'good' message. The message type shall default on power-up to Acc Y/Acc X message.

4. The checksum for the output message is calculated before the message is loaded into the SPI® registers. When the checksum is about to be calculated, the Data Bytes are stored and updates to them are inhibited. The Checksum is then calculated on the Status Byte and these 4 Data Bytes. The Status Byte can continue to be updated for a short time after the Checksum has been calculated. Therefore when the Status Byte, 4 Data Bytes and the Checksum are loaded into the SPI® register there is a small chance that the Checksum will be incorrect. It is therefore advised that if a Checksum Error is detected that the Status Byte should still be interrogated for the Status, such as BIT Fault.

5. For the status byte the following conditions apply.

7.5 CBIT

The Gemini™ sensor has a Commanded Built in Test (CBIT) function which stimulates the output to give a synthetic acceleration output. This allows the acceleration channel to be functionally tested, identifying potential failure.

CBIT can be requested using the Command Byte as detailed in Section 7.4.1. The sensor will respond by applying a fixed offset to both acceleration outputs. The offset applied depends on the CAS variant being used, see Table 7.6 for details. The offset added will have a ±20% tolerance due to MEMS tolerance effects. The time taken to apply these offsets will be less than 35ms.

The intrusive nature of CBIT is such that whilst the sensor may continue to be used to indicate acceleration, the performance is not guaranteed while CBIT is asserted.

For full performance acceleration measurement, it is recommended that 35ms is allowed to elapse following the de-assertion of CBIT to allow the sensor to settle again.

Table 7.6 CBIT Offset for CAS200 Sensor

8 Design Tools and Resources Available

The following is planned to be available from the website in the near future.

gemini Dual-Axis Accelerometer **CAS200** Technical Datasheet

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9 Cleaning

Due to the natural resonant frequency and amplification factor (' Q ') of the sensor, ultrasonic cleaning should NOT be used to clean the Gemini™ Accelerometer.

10 Soldering Information

Figure 10.1 Recommended Refl ow Solder Profi le

Figure 11.1 Part Marking

Table 11.1 Part Marking (Serial Number)

12 Packaging Information

Gemini™ sensors are supplied in tape format as either straight strips, or on either full-size or mini-reels, depending on the quantity being shipped. Table 12.1 defines the packaging method:

Table 12.1 Packaging Tape and Reel Format According to Shipping Quantity

The following information in this section defines the packaging for shipments using full-size reels.

Table 12.2 Packaging Information (Full-Size Reel)

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11 Part Markings

Table 12.3 Packaging Specification (Full-Size Reel)

Reel Information

Emboss Tape Carrier Information

Tape Information

Label for Reel Information

gemini Dual-Axis Accelerometer **CAS200** Technical Datasheet

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13 Internal Construction and Theory of Operation

Construction

Gemini™ is supplied as a PCBA surface mountable LCC ceramic packaged device. It comprises four main components; Silicon On Glass (SOG) Dual-Axis MEMS Accelerometer, ASIC and, the Package Base and Lid. The MEMS Sensors and ASIC are housed in a hermetically sealed package cavity with a nitrogen back-filled partial vacuum, this has particular advantages over sensors supplied in plastic packages which have Moisture Sensitivity Level limitations.

Figure 13.1 CAS200 Main Components

Silicon MEMS Dual-Axis Accelerometer

The Gemini™ dual-axis open loop accelerometer is a one-piece resonating silicon MEMS structure anodically bonded to top and bottom glass substrates to form a hermetically sealed Silicon on Glass (SOG) wafer sub-assembly. A DRIE bulk silicon process is used to create two orthogonal finger-like spring/ seismic proof mass structures, each measuring 1.8mm square, and with a resonant frequency of 1.8kHz to 5.2kHz. Figure 13.2 shows a schematic cross section through the SOG wafer.

Capacitive drive and pick-off signals are transmitted by wire bond interconnections, in through-glass vias, between the metallised transducer plates on the MEMS proof mass and the Gemini™ ASIC.

Multiple inter-digitated fingers create increased capacitance thus enabling a high signal-to-noise ratio. The fingers are tapered to increase the resonant frequency and also have a high aspect ratio to provide highly stable performance. The differential gaps between the static electrode fingers and those of the proof mass provide an air squeeze film with nearcritical damping.

Control of the accelerometer is handled by the Gemini™ ASIC.

Figure 13.2 Schematic Section of the Silicon On Glass Accelerometer MEMS Wafer Sub-Assembly

ASIC

The ASIC is a 3.93mm x 3.2mm device fabricated using 0.35μm CMOS process. ASIC and MEMS are physically separate and are connected electrically by using gold bond wires and thus the ASIC has no MEMS-to-ASIC internal tracking, meaning there is reduced noise pick-up. Gold bond wires also connect the ASIC to the internal bond pads on the Package Base.

Package Base and Lid

The LCC ceramic Package Base is a multi-layer aluminium oxide construction with internal bond wire pads connected through the Package Base via integral multi-level tungsten interconnects to a series of external solder pads. Similar integral interconnects in the ceramic layers connect the Lid to Vss, thus the sensitive elements are inside a Faraday shield. Internal and external pads are electroplated gold on electroplated nickel.

The Package Base incorporates a seal ring on the upper layer onto which a Kovar® metal Lid is seam welded using a rolling resistance electrode, thus creating a totally hermetic seal. Unlike other MEMS

packages available on the market, Gemini™ has a specially developed seam weld process which eliminates the potential for internal weld spatter. Inferior designs can cause dislodged weld spatter which affects reliability due to interference with the moving MEMS element.

Theory of Operation (Accelerometer)

The accelerometer contains a seismic 'proof mass' with multiple fingers suspended via a 'spring', all of which is formed in the silicon MEMS structure. The proof mass is anodically bonded to the top and bottom glass substrates and thereby fixed to the Gemini[™] Package Base.

When the Gemini™ sensor is subjected to a linear acceleration along its sensitive axis the proof mass tends to resist motion due to its own inertia, therefore the mass and it's fingers becomes displaced with respect to the interdigitated fixed electrode fingers. Gas between the fingers provides a damping effect. This displacement induces a differential capacitance between the moving and fixed silicon fingers which is proportional to the applied acceleration.

Capacitor plate groups are electrically connected in pairs at the top and bottom of the proof mass. In-phase and anti-phase waveforms are applied by the Gemini[™] ASIC separately to the 'left' and 'right' finger groups. The demodulated waveforms provide a signal output proportional to linear acceleration.

Figures 13.3(a) and 13.4(b) provide schematics of the accelerometer structure and control loop respectively.

Fixed Electrode 1 | Fixed Electrode 2 Sensing axis Fixed support

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Proof mass (includes fingers)

Figure 13.3(a) Schematic of Accelerometer **Structure**

Figure 13.4(b) Schematic of Accelerometer Control Loop

14 Patent Applications

The following patent applications have been filed for the Gemini™ Accelerometers:

Notes

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